

IN THE SPECIFICATION:

On page 1, 2ND paragraph, line 9, titled "CROSS REFERENCE TO RELATED APPLICATION":

CROSS REFERENCE TO RELATED APPLICATIONS

This application claims priority to, and is a continuation of, the co-pending U.S. patent application number 09/807,266 filed June 11, 2001, which is a 371 application of PCT/US99/23717 filed October 8, 1999 and incorporates it in by reference in its entirety, which claims the benefit of U.S. Provisional Application Serial No. 60/103,790 filed October 9, 1998 [is claimed].

Page 9, 3rd paragraph, line 29 and continuing onto page 10:

Turning with specificity to the figures, Fig. 1 schematically illustrates the lithographically induced self-assembly of the present invention. Onto the substrate 31 is layered a material 33, which, in the preferred embodiment, is a thin layer of homopolymer, preferably polymethyl-methacrylate (PMMA). The PMMA was first spun on substrate 31, in this case, a silicon wafer having a substantially plain flat surface, followed by baking 80°C to drive out the solvent. Next a mask 35, typically made of silicon dioxide, with a protruding pattern 37 on its surface that faces a deformable material 33 is placed above the PMMA film 33. As is shown in Fig. 1, the mask 35 is separated, using a spacer 39, from the PMMA by several hundred nanometers. The distance between the protrusion 37 and film 33 is preferably in the range of about 10nm to about 100nm, more preferable 50 nm to 800nm, and ~~never~~ even more preferably that about 100nm to about 700nm. The spacer 39 may be either integrally formed with the mask or a separate element (see e.g. Fig. 12).

On page 5, line 7, please add the following paragraph:

“Embodiments of the present invention include an article having nanoscale patterning, the article being comprised of a plurality of self assembled pillars, the plurality of pillars having a height ranging from above 1 nm to below 1000 nm; the height of the plurality of pillars may be in the range of about 100 nm to about 700 nm; the height of the plurality of pillars may be in the range of about 250 nm to about 550 nm. The self assembled pillar on the substrate having a height ranging from above 1 nm to below 1000 nm may have a diameter with the pillar height to pillar diameter ratio being in a range of about 0.1 to about 0.5. The article being comprised of a plurality of self assembled pillars having a height ranging from above 1 nm to below 1000 nm may be a plurality of self assembled pillars on the substrate that are in a periodic array. The article may have nanoscale patterning, the article being comprising a plurality of self assembled pillars with the plurality of pillars having a height ranging from above 1 nm to below 1000 nm wherein the plurality of self assembled pillars on the substrate has a period of about 1 μm to about 10 μm .”